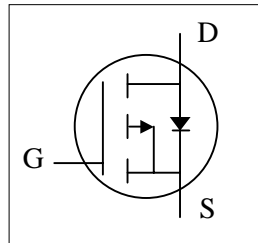


**AP6679GH/J****RoHS-compliant Product****Advanced Power  
Electronics Corp.***P-CHANNEL ENHANCEMENT MODE**POWER MOSFET*

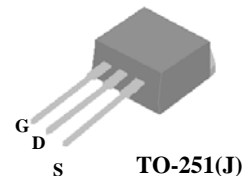
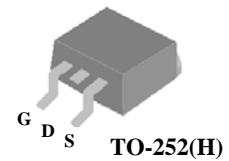
- ▼ Lower On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic



$BV_{DSS}$	-30V
$R_{DS(ON)}$	9m $\Omega$
$I_D$	-75A

**Description**

The TO-252 package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP6679GJ) is available for low-profile applications.

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	+25	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>3</sup>	-75	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	-50	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-300	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	89	W
	Linear Derating Factor	0.71	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Data**

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.4	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^\circ\text{C}/\text{W}$



## AP6679GH/J

### Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1mA$	-	-0.03	-	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-30A$	-	-	9	m $\Omega$
		$V_{GS}=-4.5V, I_D=-24A$	-	-	15	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-	-3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=-10V, I_D=-24A$	-	34	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	$\mu A$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{DS}=-24V, V_{GS}=0V$	-	-	-25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 25V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=-16A$	-	42	67	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=-24V$	-	6	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=-4.5V$	-	25	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=-15V$	-	11	-	ns
$t_r$	Rise Time	$I_D=-16A$	-	35	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=-10V$	-	58	-	ns
$t_f$	Fall Time	$R_D=0.94\Omega$	-	78	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	2870	4590	pF
$C_{oss}$	Output Capacitance	$V_{DS}=-25V$	-	960	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0MHz$	-	740	-	pF

### Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=-24A, V_{GS}=0V$	-	-	-1.2	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=-16A, V_{GS}=0V,$	-	47	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=-100A/\mu s$	-	43	-	nC

#### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Package limitation current is -75A .

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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# AP6679GH/J

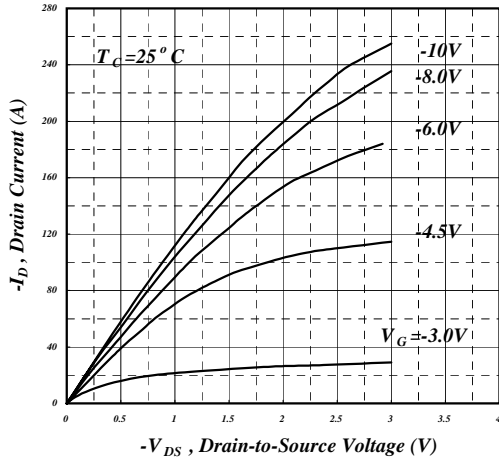


Fig 1. Typical Output Characteristics

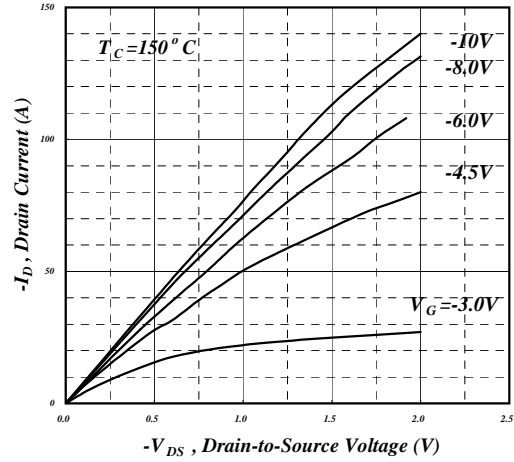


Fig 2. Typical Output Characteristics

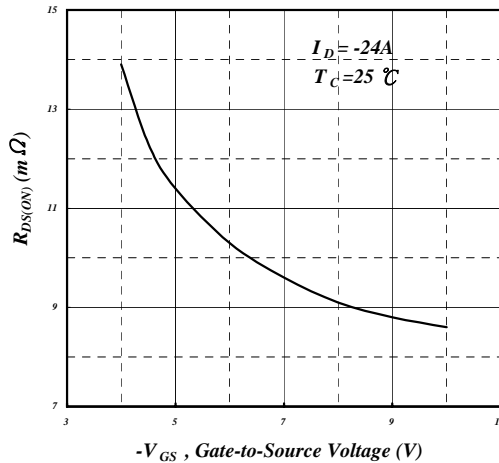


Fig 3. On-Resistance v.s. Gate Voltage

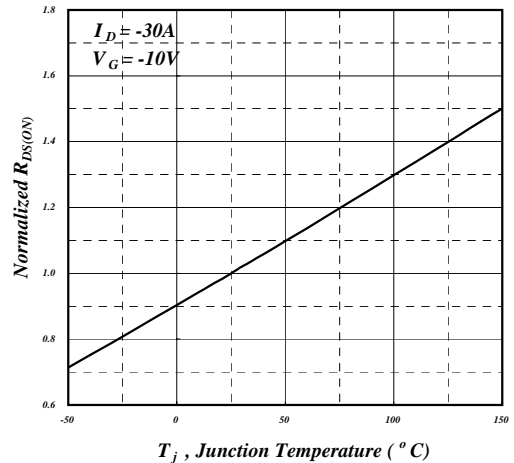


Fig 4. Normalized On-Resistance v.s. Junction Temperature

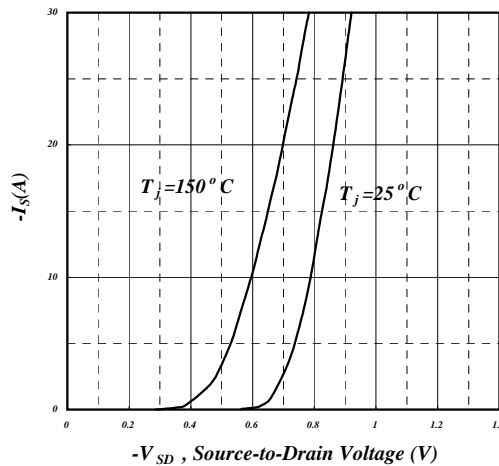


Fig 5. Forward Characteristic of Reverse Diode

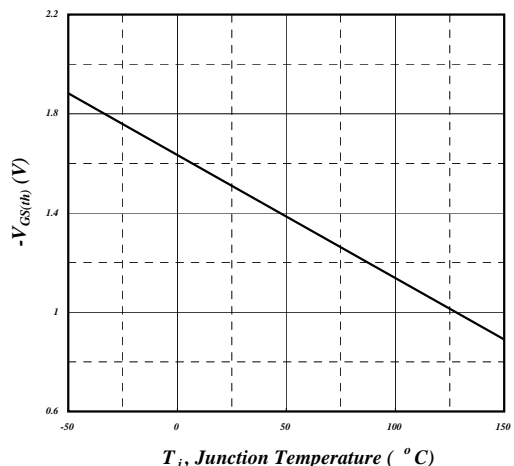


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



# AP6679GH/J

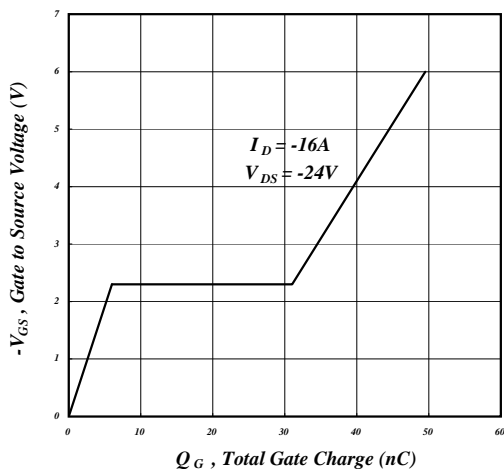


Fig 7. Gate Charge Characteristics

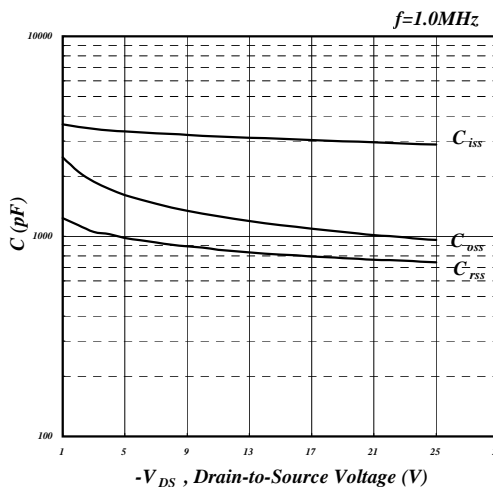


Fig 8. Typical Capacitance Characteristics

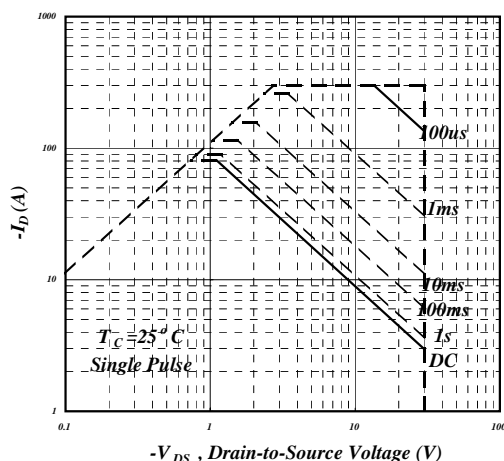


Fig 9. Maximum Safe Operating Area

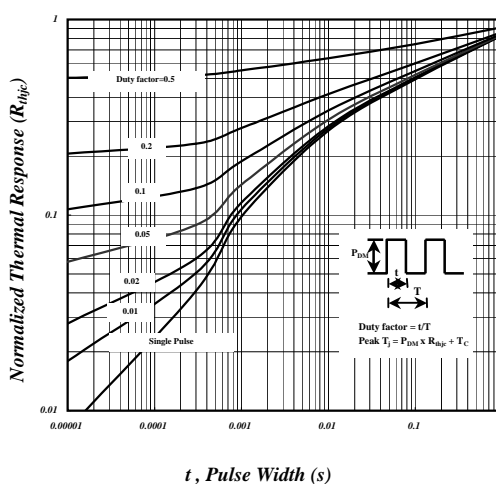


Fig 10. Effective Transient Thermal Impedance

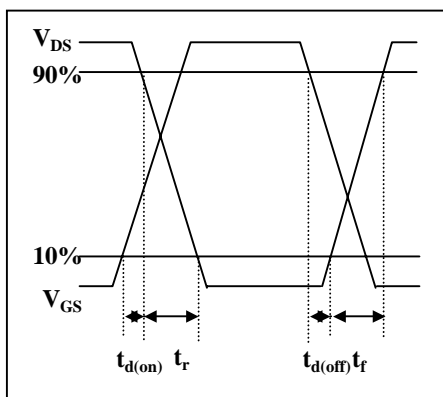


Fig 11. Switching Time Waveform

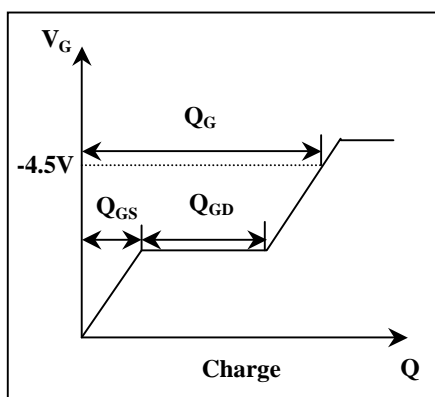
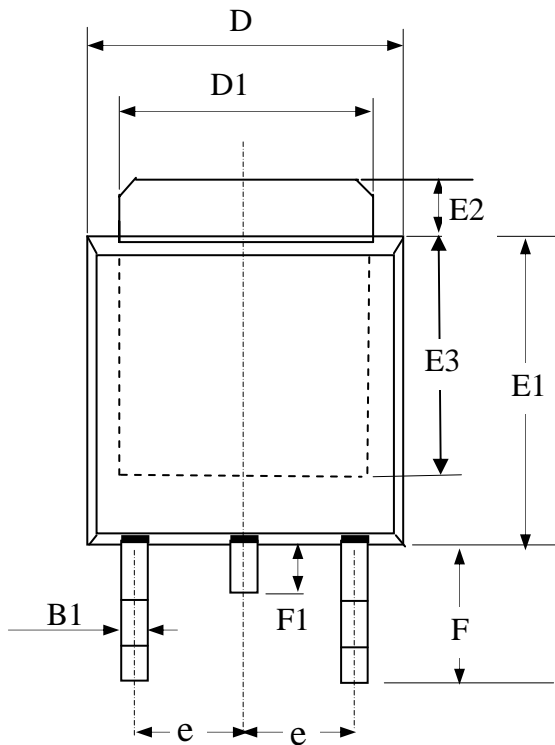


Fig 12. Gate Charge Waveform

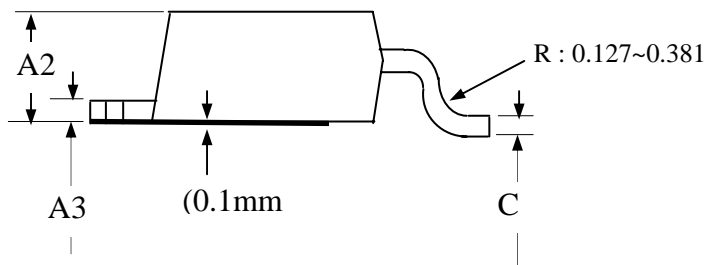


## Package Outline : TO-252



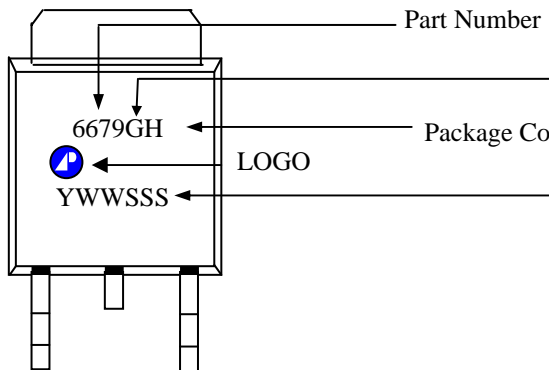
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



## Part Marking Information & Packing : TO-252

Laser Marking



Meet Rohs requirement  
for low voltage MOSFET only

Date Code (YWWSSS)

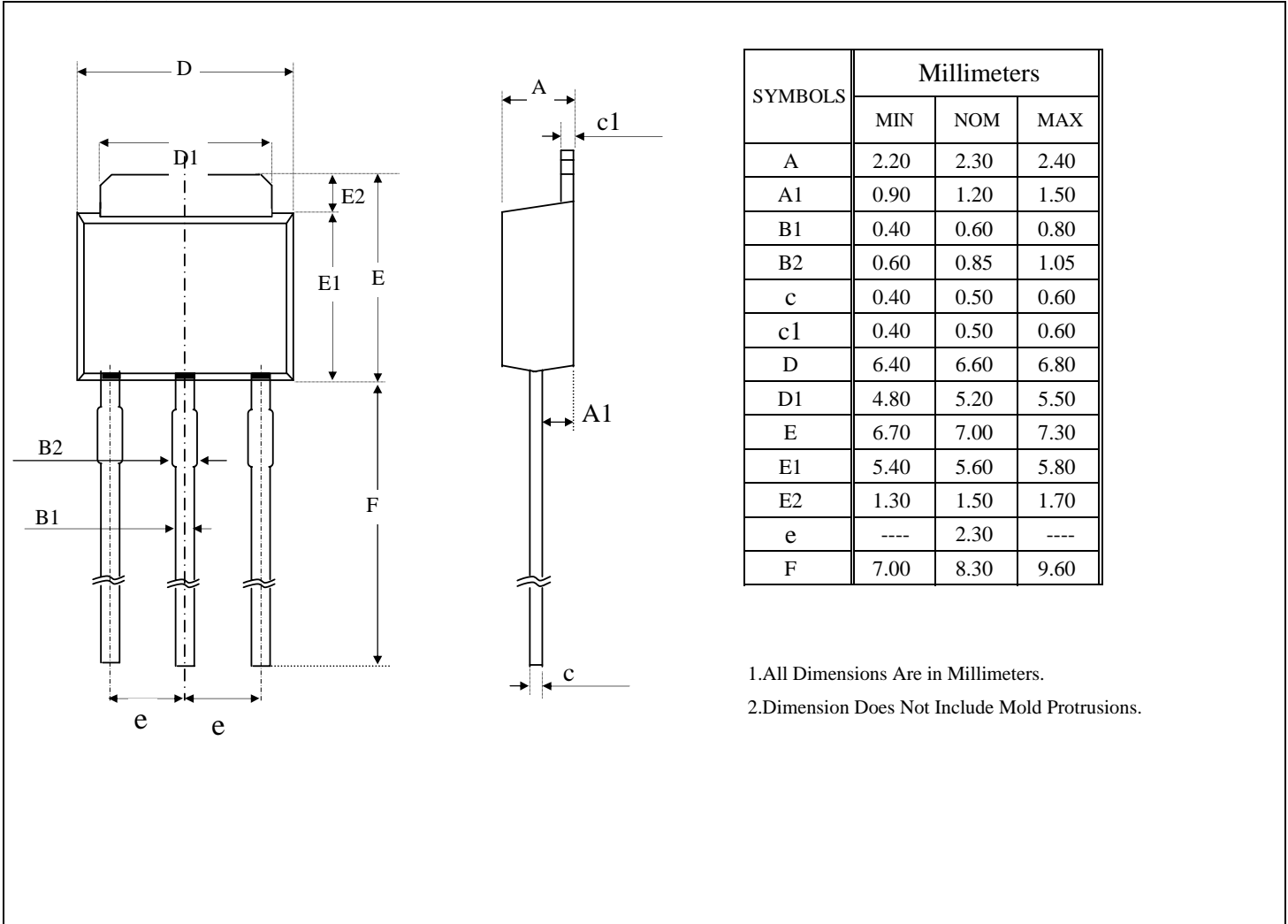
Y : Last Digit Of The Year

WW : Week

SSS : Sequence



Package Outline : TO-251



Part Marking Information & Packing : TO-251

